TOSHIBA Transistor GaAs NPN Epitaxial Mesa Type

MTG3S01AP

VHF-UHF Low-Noise, Low-Distortion Amplifier Application

FEATURES

- Low Noise Figure: NF=1.0dB (@f=1GHz)
- High Gain: |S21e|²=11.0dB (@f=1GHz)

Marking



Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	9	V
Collector-emitter voltage	V _{CEO}	7	V
Emitter-base voltage	V _{EBO}	3	V
Collector-current	Ι _C	90	mA
Base-current	Ι _Β	7.5	mA
Collector power dissipation	Pc(Note1,2)	300	mW
	P _C (Note2)	630	mW
Junction temperature	Тj	150	°C
Storage temperature range	T _{stg}	-55~150	°C



Weight:0.05g

Note 1: Reference Pad Dimension.

Note 2: The device is mounted on a glass-epoxy printed circuit board (645mm² X0.8 mm (t))

Unit:mm

Microwave Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Transition frequency	f _T	V _{CE} =5V, I _C =50mA	12	15	_	GHz
Insertion gain -	S21e ² (1)	V _{CE} =5V, I _C =50mA, f=500MHz	_	16.5	_	dB
	S21e ² (2)	V _{CE} =5V, I _C =50mA, f=1GHz	9.5	11.0	_	dB
Noise figure	NF(1)	V _{CE} =5V, I _C =10mA, f=500MHz Zs=ZL=50	_	0.7	_	dB
	NF(2)	V _{CE} =5V, I _C =10mA, f=1GHz Zs=ZL=50	_	1.0	1.5	dB
	NF(3)	V _{CE} =5V, I _C =50mA, f=1GHz Zs=ZL=50	_	1.3	_	dB
3 rd order intermodulation distortion output intercept point	OIP3	V _{CE} =5V,I _C =50mA,f=100MHz, f=1MHz	_	34	_	dBmW

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} =8V, I _E =0	_	_	1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =2V, I _C =0		—	1	μA
DC current gain	hFE	V _{CE} =5V, I _C =50mA	230	—	450	-
Output capacitance	C _{ob}	V _{CB} =5V, I _E =0, f=1MHz	_	1.18	—	pF
Reverse transfer capacitance	C _{re}	V _{CB} =5V, I _E =0, f=1MHz (Note 1)		0.87	_	pF

Note 1: C_{re} is measured using a 3-terminal method with capacitance bridge.

Caution: 1. This device is sensitive to electrostatic discharge.

Be sure to provide all tools and equipment with adequate grounding.

- 2. This device may be subject to damage from thermal stress. Observe the precautions below.
 - Avoid using soldering irons for soldering under mass production.
 - A device once removed from a printed circuit board by using a soldering iron should not be re-used for mass-produced equipment.
 - If using soldering irons to perform soldering when conducting any kind of evaluation, be sure to complete the soldering within ten seconds at a temperature of 260° C or less.

roshiba

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4.0

2.0

0.0

1









10



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100

Associated gain Ga(dB)

100







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